

**AMENDMENTS TO THE CLAIMS:**

This listing of claims will replace all prior versions, and listings, of claims in the application:

1. (Currently Amended) A display device comprising~~[[ : ]]~~ plural pixels, at least one of the plural pixels comprising:

~~plural groups including a light emitting element and a thin film transistor which is connected to the light emitting element;~~

~~a first thin film transistor, a second thin film transistor, and a third thin film transistor; a first gate signal line, and a second gate signal line, a source signal line, and a current supply line,~~

~~wherein a gate of the first thin film transistor is electrically connected to the first gate signal line and a second terminal of the third thin film transistor,~~

~~wherein a first terminal of the first thin film transistor is electrically connected to the source signal line,~~

~~wherein a second terminal of the first thin film transistor is electrically connected to a gate of the second thin film transistor and a first terminal of the third thin film transistor,~~

~~wherein a first terminal of the second thin film transistor is electrically connected to the current supply line,~~

~~wherein a second terminal of the second thin film transistor is electrically connected to the light emitting element,~~

~~wherein a second terminal of the third thin film transistor is electrically connected to the first gate signal line,~~

~~wherein a gate of the third thin film transistor is electrically connected to the second gate signal line, and~~

~~wherein a channel of the second thin film transistor is folded and orients in a plurality of directions, and~~

~~wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.~~

2. (Currently Amended) A display device according to claim 1,

wherein [[the]] a channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width of the second thin film transistor, respectively.

3. (Currently Amended) A display device according to claim 1,

wherein the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.

4. (Currently Amended) A display device comprising[[::]] plural pixels, at least one of the plural pixels comprising;

~~plural groups including a thin film transistor and a light emitting element in which brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage-drain current characteristic of the thin film transistor;~~

a first thin film transistor, a second thin film transistor, and a third thin film transistor;  
a first gate signal line, and a second gate signal line, a source signal line, and a current supply line,

wherein a gate of the first thin film transistor is electrically connected to the first gate signal line and a second terminal of the third thin film transistor,

wherein a first terminal of the first thin film transistor is electrically connected to the source signal line,

wherein a second terminal of the first thin film transistor is electrically connected to a gate of the second thin film transistor and a first terminal of the third thin film transistor,

wherein a first terminal of the second thin film transistor is electrically connected to the current supply line,

wherein a second terminal of the second thin film transistor is electrically connected to the light emitting element,

wherein a second terminal of the third thin film transistor is electrically connected to the first gate signal line,

wherein a gate of the third thin film transistor is electrically connected to the second gate signal line, and

wherein a channel of the second thin film transistor is folded and orients in a plurality of directions, and

wherein brightness of the light emitting element in which brightness is arranged to be fluctuated depending on an ON current value in a saturation region of a drain-voltage-drain current characteristic of the second thin film transistor.

wherein an absolute value of a fluctuation rate in an ON current value in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12 %.

5. (Currently Amended) A display device according to claim 4,

wherein [[the]] a channel length of the first thin film transistor and the second thin film transistor is at least 5 times as long as a gate width of the second thin film transistor, respectively.

6. (Currently Amended) A display device according to claim 4,

wherein the first thin film transistor and the second thin film transistor comprises a semiconductor layer which is formed by irradiating with a pulsed laser beam.

7. (Currently Amended) A display device comprising plural pixels including:

a driving thin film transistor, a switching thin film transistor, an erasing thin film transistor, a light emitting element which is connected to a second terminal of the driving thin film transistor; and

a first gate signal line, and a second gate signal line, a source signal line, and a current supply line,

wherein a gate of the switching thin film transistor is electrically connected to the first gate signal line and a second terminal of the erasing thin film transistor,

wherein a first terminal of the switching thin film transistor is electrically connected to the source signal line,

wherein a second terminal of the switching thin film transistor is electrically connected to a gate of the driving thin film transistor and a first terminal of the erasing thin film transistor,

wherein a first terminal of the driving thin film transistor is electrically connected to the current supply line,

wherein a second terminal of the erasing thin film transistor is electrically connected to the first gate signal line,

wherein a gate of the erasing thin film transistor is electrically connected to the second gate signal line, and

wherein brightness is fluctuated depending on an ON current value in a saturation region of a drain voltage drain current characteristic of the driving thin film transistor;

wherein a channel of the driving thin film transistor is folded and orients in a plurality of directions, and

wherein an absolute value of a fluctuation rate of the ON current value in a saturation region of the driving thin film transistor included in each a first pixel and a second pixel which is adjacent to the first pixel is at most 12%.

8. (Currently Amended) A display device according to claim 7,

wherein a channel length of the driving thin film transistor is at least 5 times as long as a gate width of the driving thin film transistor.

9. (Currently Amended) A display device according to claim 7,

wherein the driving thin film transistor comprises a semiconductor layer formed by irradiating with a pulsed laser beam.

10. (Currently Amended) An electronic device having the display device according to claim 1,

wherein [[said]] the electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

11. (Currently Amended) An electronic device having the display device according to claim 4,

wherein [[said]] the electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a mobile telephone.

12. (Currently Amended) An electronic device having the display device according to claim 7,

wherein [[said]] the electronic device is selected from the group consisting of a display device, a video camera, a notebook computer, a personal digital assistant, a digital still camera, and a cellular phone.

13. (Previously Presented) A cellular phone comprising a main body, a display portion, a voice output portion, an operation switch, and an antenna[[;]], ~~said cellular phone comprising:~~

wherein the display portion comprises plural [[groups]] pixels,

wherein at least one of the plural pixels including includes a light emitting element, [[and]] a first thin film transistor, a second thin film transistor, a third thin film transistor, a first gate signal line, a second gate signal line, a source signal line, and a current supply line, which is connected to the light emitting element;

wherein a gate of the first thin film transistor is electrically connected to the first gate signal line and a second terminal of the third thin film transistor,

wherein a first terminal of the first thin film transistor is electrically connected to the source signal line,

wherein a second terminal of the first thin film transistor is electrically connected to a gate of the second thin film transistor and a first terminal of the third thin film transistor,

wherein a first terminal of the second thin film transistor is electrically connected to the current supply line,

wherein a second terminal of the second thin film transistor is electrically connected to the light emitting element,

wherein a second terminal of the third thin film transistor is electrically connected to the first gate signal line,

wherein a gate of the third thin film transistor is electrically connected to the second gate signal line, and

wherein a channel of the second thin film transistor is folded and orients in a plurality of directions,and

~~wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.~~

14. (Currently Amended) A notebook computer comprising a main body, a case, a display portion, and a keyboard[[;]],

said notebook computer comprising:

wherein the display portion comprises plural [[groups]] pixels,

wherein at least one of the plural pixels including includes a light emitting element,  
[[and]] a first thin film transistor, a second thin film transistor, a third thin film transistor, a  
first gate signal line, a second gate signal line, a source signal line, and a current supply line,  
which is connected to the light emitting element;

wherein a gate of the first thin film transistor is electrically connected to the first gate signal line and a second terminal of the third thin film transistor,

wherein a first terminal of the first thin film transistor is electrically connected to the source signal line,

wherein a second terminal of the first thin film transistor is electrically connected to a gate of the second thin film transistor and a first terminal of the third thin film transistor,

wherein a first terminal of the second thin film transistor is electrically connected to the current supply line,

wherein a second terminal of the second thin film transistor is electrically connected to the light emitting element,

wherein a second terminal of the third thin film transistor is electrically connected to the first gate signal line,

wherein a gate of the third thin film transistor is electrically connected to the second gate signal line, and

wherein a channel of the second thin film transistor is folded and orients in a plurality of directions,and

~~wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.~~

15. (Currently Amended) A semiconductor device comprising~~[[::]]~~ plural pixels, at least one of the plural pixels comprising:

~~a light emitting element and a thin film transistor which is connected to the light emitting element;~~

~~a first thin film transistor, a second thin film transistor, and a third thin film transistor; a first gate signal line, and a second gate signal line, a source signal line, and a current supply line,~~

~~wherein a gate of the first thin film transistor is electrically connected to the first gate signal line and a second terminal of the third thin film transistor,~~

~~wherein a first terminal of the first thin film transistor is electrically connected to the source signal line,~~

~~wherein a second terminal of the first thin film transistor is electrically connected to a gate of the second thin film transistor and a first terminal of the third thin film transistor,~~

~~wherein a first terminal of the second thin film transistor is electrically connected to the current supply line,~~

~~wherein a second terminal of the second thin film transistor is electrically connected to the light emitting element,~~

~~wherein a second terminal of the third thin film transistor is electrically connected to the first gate signal line,~~

~~wherein a gate of the third thin film transistor is electrically connected to the second gate signal line, and~~

~~wherein a channel of the second thin film transistor is folded and orients in a plurality of directions, and~~

~~wherein an absolute value of a fluctuation rate of an ON current in a saturation region of a first thin film transistor included in a first group of said plural groups and a second thin film transistor included in a second group of said plural groups which is adjacent to the first group is at most 12%.~~

16. (Original) An electronic device having the semiconductor device according to claim 15,  
wherein said electronic device is selected from the group consisting of a display  
device, a video camera, a notebook computer, a personal digital assistant, a digital still  
camera, and a cellular phone.

17.-48. (Canceled)

49. (New) The display device according to claim 1,  
wherein the first thin film transistor is an N-channel thin film transistor,  
wherein the second thin film transistor is a P-channel thin film transistor, and  
wherein the third thin film transistor is an N-channel thin film transistor.

50. (New) The display device according to claim 4,  
wherein the first thin film transistor is an N-channel thin film transistor,  
wherein the second thin film transistor is a P-channel thin film transistor, and  
wherein the third thin film transistor is an N-channel thin film transistor.

51. (New) The display device according to claim 7,  
wherein the switching thin film transistor is an N-channel thin film transistor,  
wherein the driving thin film transistor is a P-channel thin film transistor, and  
wherein the erasing thin film transistor is an N-channel thin film transistor.

52. (New) The cellular phone according to claim 13,  
wherein the first thin film transistor is an N-channel thin film transistor,  
wherein the second thin film transistor is a P-channel thin film transistor, and  
wherein the third thin film transistor is an N-channel thin film transistor.

53. (New) The notebook computer according to claim 14,  
wherein the first thin film transistor is an N-channel thin film transistor,  
wherein the second thin film transistor is a P-channel thin film transistor, and  
wherein the third thin film transistor is an N-channel thin film transistor.

54. (New) The semiconductor device according to claim 15,  
wherein the first thin film transistor is an N-channel thin film transistor,  
wherein the second thin film transistor is a P-channel thin film transistor, and  
wherein the third thin film transistor is an N-channel thin film transistor.